

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI VHB25-28S** is Designed for Class C, 28 V High Band Applications up to 175 MHz.

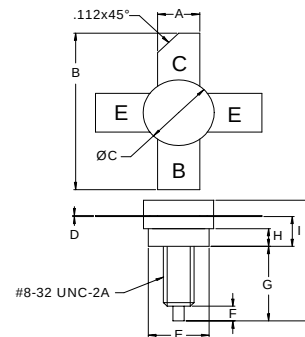
FEATURES:

- Common Emitter
- $P_G = 8.5$ dB at 25 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	40 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	4.4 $^\circ\text{C/W}$

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10725

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200$ mA			35			V
BV_{CES}	$I_C = 200$ mA			65			V
BV_{EBO}	$I_E = 10$ mA			4.0			V
I_{CBO}	$V_E = 28$ V					2.0	mA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 200$ mA		5		---	---
C_{OB}	$V_{CB} = 28$ V	$f = 1.0$ MHz				50	pF
f_T	$V_{CE} = 10$ V	$I_C = 200$ mA	$f = 100$ MHz	250			MHz
P_G η_C	$V_{CC} = 28$ V	$P_{OUT} = 25$ W	$f = 175$ MHz	8.5	60		dB %